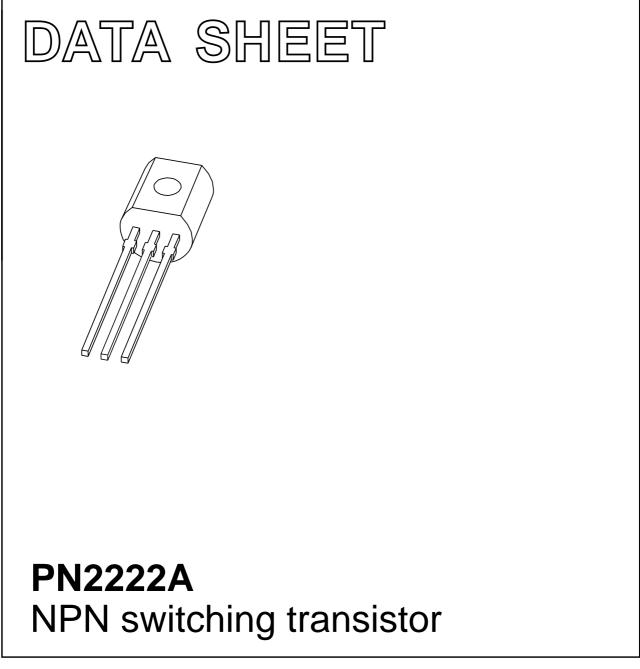
# DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 May 21 2004 Oct 11



#### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

#### APPLICATIONS

• General purpose switching and linear amplification.

#### DESCRIPTION

NPN switching transistor in a TO-92; SOT54 plastic package. PNP complement: PN2907A.

#### PINNING

| PIN | DESCRIPTION |  |
|-----|-------------|--|
| 1   | collector   |  |
| 2   | base        |  |
| 3   | emitter     |  |

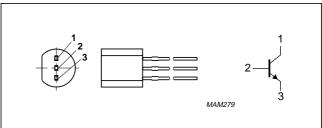


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

#### **ORDERING INFORMATION**

|             |        | PACKAGE   |         |  |  |
|-------------|--------|---|---------|--|--|
| ITFE NUMBER | NAME   | DESCRIPTION   | VERSION |  |  |
| PN2222A     | SC-43A | plastic single-ended leaded (through hole) package; 3 leads |         |  |  |

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                   | CONDITIONS                   | MIN. | MAX. | UNIT |
|------------------|-----------------------------|------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage      | open emitter                 | -    | 75   | V    |
| V <sub>CEO</sub> | collector-emitter voltage   | open base                    | -    | 40   | V    |
| V <sub>EBO</sub> | emitter-base voltage        | open collector               | -    | 6    | V    |
| I <sub>C</sub>   | collector current (DC)      |                              | -    | 600  | mA   |
| I <sub>CM</sub>  | peak collector current      |                              | _    | 800  | mA   |
| I <sub>BM</sub>  | peak base current           |                              | -    | 200  | mA   |
| P <sub>tot</sub> | total power dissipation     | $T_{amb} \le 25 \ ^{\circ}C$ | _    | 500  | mW   |
| T <sub>stg</sub> | storage temperature         |                              | -65  | +150 | °C   |
| Tj               | junction temperature        |                              | -    | 150  | °C   |
| T <sub>amb</sub> | ambient temperature -65 +15 |                              | +150 | °C   |      |

### **PN2222A**

### PN2222A

### THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient | note 1     | 250   | K/W  |

#### Note

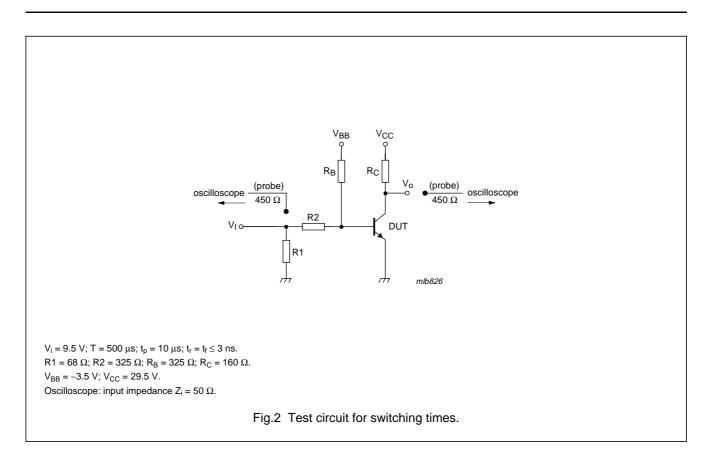
1. Transistor mounted on an FR4 printed-circuit board.

#### CHARACTERISTICS

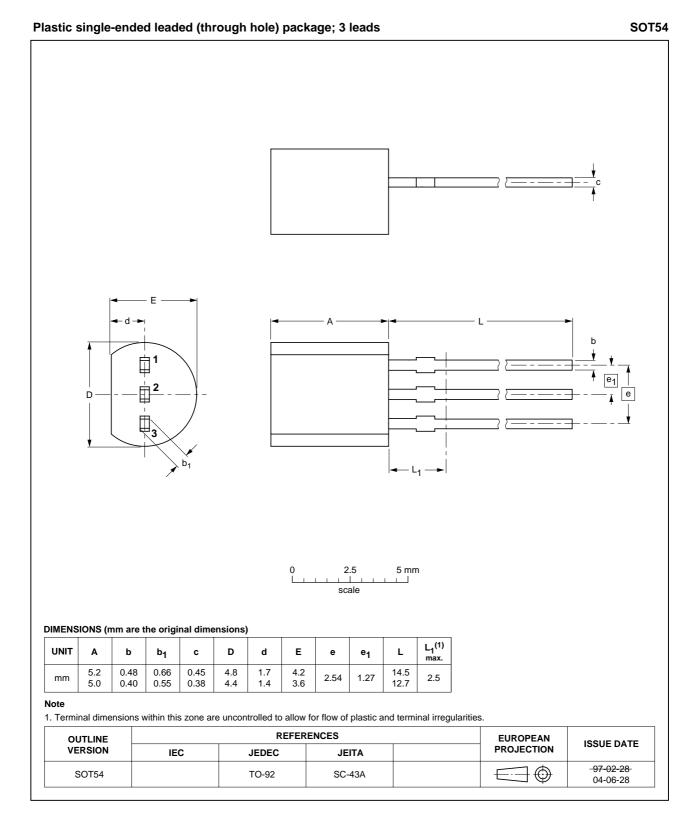
 $T_{amb}$  = 25 °C unless otherwise specified.

| SYMBOL             | PARAMETER                            | CONDITIONS   | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|--|------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off current       | $V_{CB} = 60 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}$                                    | -    | 10   | nA   |
|                    |                                      | V <sub>CB</sub> = 60 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 125 °C                          | -    | 10   | μA   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | $V_{EB} = 3 \text{ V}; \text{ I}_{C} = 0 \text{ A}$  | _    | 10   | nA   |
| h <sub>FE</sub>    | DC current gain                      | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 0.1 mA  | 35   | -    |      |
|                    |                                      | $V_{CE} = 10 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$  | 50   | -    |      |
|                    |                                      | $V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}$   | 75   | -    |      |
|                    |                                      | $V_{CE} = 10 \text{ V}; \text{ I}_{C} = 10 \text{ mA}; \text{ T}_{j} = -55 \text{ °C}$         | 35   | -    |      |
|                    |                                      | V <sub>CE</sub> = 1 V; I <sub>C</sub> = 150 mA   | 50   | -    |      |
|                    |                                      | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 150 mA  | 100  | 300  |      |
|                    |                                      | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 500 mA  | 40   | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA  | -    | 300  | mV   |
|                    |                                      | $I_{\rm C} = 500 \text{ mA}; I_{\rm B} = 50 \text{ mA}$  | 1    | -    | V    |
| V <sub>BEsat</sub> | base-emitter saturation voltage      | I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA  | 0.6  | 1.2  | V    |
|                    |                                      | $I_{\rm C} = 500 \text{ mA}; I_{\rm B} = 50 \text{ mA}$  | _    | 2    | V    |
| C <sub>c</sub>     | collector capacitance                | $V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$ | -    | 8    | pF   |
| C <sub>e</sub>     | emitter capacitance                  | $V_{EB} = 500 \text{ mV}; I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$                          | -    | 25   | pF   |
| f <sub>T</sub>     | transition frequency                 | V <sub>CE</sub> = 20 V; I <sub>C</sub> = 20 mA; f = 100 MHz                                    | 300  | -    | MHz  |
| F                  | noise figure                         | $V_{CE}$ = 5 V; I <sub>C</sub> = 100 µA; R <sub>S</sub> = 1 kΩ;<br>f = 1 kHz                   | -    | 4    | dB   |
| Switching t        | imes (between 10 % and 90 % level    | ls); see Fig.2   |      |      |      |
| t <sub>on</sub>    | turn-on time                         | I <sub>Con</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;   | -    | 35   | ns   |
| t <sub>d</sub>     | delay time                           | I <sub>Boff</sub> = −15 mA; T <sub>amb</sub> = 25 °C   | -    | 15   | ns   |
| t <sub>r</sub>     | rise time                            | 1  | -    | 20   | ns   |
| t <sub>off</sub>   | turn-off time                        | 1  | -    | 250  | ns   |
| t <sub>s</sub>     | storage time                         | 1  | -    | 200  | ns   |
| t <sub>f</sub>     | fall time                            | 1  | _    | 60   | ns   |

### PN2222A



#### PACKAGE OUTLINE



PN2222A

PN2222A

#### DATA SHEET STATUS

| LEVEL | DATA SHEET<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)(3)</sup> | DEFINITION   |
|-------|-------------------------------------|-------------------------------------|--|
| I     | Objective data                      | Development                         | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
| 11    | Preliminary data                    | Qualification                       | This data sheet contains data from the preliminary specification.<br>Supplementary data will be published at a later date. Philips<br>Semiconductors reserves the right to change the specification without<br>notice, in order to improve the design and supply the best possible<br>product.             |
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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Oct 11

Document order number: 9397 750 13618

SCA76

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